

INFORMATION DISCLOSURE CITATION. (USE SEVERAL SHEETS IF NECESSARY)				ATTY. DOCKET NO. Serie 6550 CIP		SERIAL NO. 10/591,629	
				APPLICANT(S) Ashutosh MISRA, et al.			
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Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date
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/A.K./	A2	US 2004 0198069	10/07/2004	Metzner et al.			
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/A.K./	C1	International Search Report for PCT/IB2005/000522	
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/A.K./	C3	Ohshita, Y. et al. <i>Hf_{1-x}Si_xO₂ deposition by metal organic chemical vapor deposition using the Hf(NEt₂)₄/SiH(NEt₂)₃/O₂ gas system</i> , Preparation and Characterization, Elsevier, Sequola, NL, vol. 416, no. 1-2, September 2, 2002, pp. 208-211	
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/A.K./	C5	Applied Physics Letters, vol. 80, no. 13, pp. 2362-2364, April 2002	

Examiner /Arman Khosraviani/	Date Considered 09/12/2007
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